AMENDMENTS TO THE CLAIMS

Claims 1-169 (Canceled)

170. (currently amended) A semiconductor component comprising:

a thinned semiconductor die having an outline, a circuit side, a planarized back side, four peripheral edges, and a plurality of die contacts on the circuit side;

a plurality of contact bumps on the die contacts;

a planarized first polymer layer covering the circuit side, the contact bumps and the peripheral edges, the first polymer layer having edge polymer layers ~~of a selected thickness on~~ covering and rigidifying the peripheral edges;

a planarized second polymer layer covering the back side, the first polymer layer and the second polymer layer encapsulating the die on six sides such that the component has a chip scale outline corresponding to the outline of the die plus ~~the selected thickness of~~ the edge polymer layers; and

a plurality of terminal contacts on the contact bumps.

171. (currently amended) The semiconductor component of claim 170 wherein the die comprises a tested and burned in die and the component comprises a known good component (KGC).
~~is initially contained on a semiconductor wafer and is tested and burned in on the wafer~~.

172. (previously presented) The semiconductor component of claim 170 wherein the contact bumps comprise metal bumps in a dense area array.

173. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts comprise conductive bumps or balls in a grid array.

174. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer and the contact bumps have a same planar surface.

175. (currently amended) The semiconductor component of claim 170 wherein the second polymer layer covers planarized edges of the edge polymer layers.
~~layer has a second planar surface.~~

176. (previously presented) The semiconductor component of claim 170 further comprising a plurality of conductive vias in the thinned die in electrical communication with the die contacts and with the terminal contacts.

177. (previously presented) The semiconductor component of claim 176 further comprising a plurality of second die contacts on the second polymer layer in electrical communication with the conductive vias.

178. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a photopolymer.

179. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a wafer level underfill.

Claims 180-261 (canceled)

262. (currently amended) The semiconductor component of claim 170 wherein the contact bumps comprise planarized surfaces.
~~backside comprises a planar surface.~~

263. (previously presented) The semiconductor component of claim 170 wherein the backside comprises a polished surface.

264. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a tape material.

265. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer on each edge comprises a portion of a polymer filled trench.

266. (currently amended) The semiconductor component of claim 170 wherein the edge polymer layers and the back side have a same planar surface.
~~second polymer layer includes at least one pin one indicator.~~

267. (currently amended) The semiconductor component of claim 170 wherein the edge polymer layers have a selected thickness which is different than a thickness of the first polymer layer.
~~first polymer layer includes at least one pin one indicator.~~

268. (previously presented) The semiconductor component of claim 170 wherein the thinned die comprises a tested and burned in die.

269. (previously presented) The semiconductor component of claim 170 wherein the thinned die is contained

on a semiconductor wafer having a polymer support dam proximate to edges thereof.

270. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises a first polymer material and the second polymer layer comprises a second polymer material.

271. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises parylene.

272. (withdrawn) The semiconductor component of claim 170 wherein the edge polymer layers form a recess and the second polymer layer is within the recess.